

AM4812M8VR-VB Datasheet

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (Ω)	I _D (A) ^a	Q _g (Typ.)			
30	0.008 at V _{GS} = 10 V	13	6.1 nC			
	0.011 at V _{GS} = 4.5 V	11	0.1110			

SO-8

Top View

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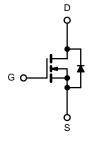
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FEATURES

- · Halogen-free
- Trench Power MOSFET
- Optimized for High-Side Synchronous Rectifier Operation
- 100 % R_g Tested
- 100 % UIS Tested

APPLICATIONS

- Notebook CPU Core
 - High-Side Switch



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	S T _A = 25 °C, unles	s otherwise no	oted	
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	± 20	7 v
	T _C = 25 °C		13	
Continuous Proin Current (T. – 150 °C)	T _C = 70 °C	,	10	
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	- I _D	9 ^{b, c}	
	T _A = 70 °C		7 ^{b, c}	
Pulsed Drain Current	I _{DM}	45	A	
Continuous Course Desir Diede Current	T _C = 25 °C	- I _S	3.7	
Continuous Source-Drain Diode Current	T _A = 25 °C		2.0 ^{b, c}	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	20	
Avalanche Energy	L = 0.1 IIII	E _{AS}	21	mJ
	T _C = 25 °C		4.1	
Manianum Davian Disabation	T _C = 70 °C	В	2.5	W
Maximum Power Dissipation	T _A = 25 °C	P _D	2,2 ^{b, c}	¬ vv
	T _A = 70 °C		1.3 ^{b, c}	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R_{thJA}	39	55	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	25	29	C/VV	

Notes:

- a. Base on T_C = 25 °C.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. Maximum under Steady State conditions is 85 °C/W.



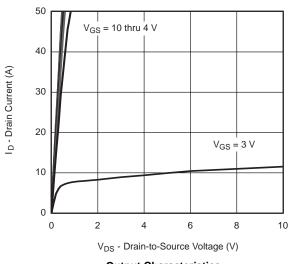
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 250A		26		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_{J}$	I _D = 250 μA		- 6			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		3.0	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zana Oata Valla na Busin Oanna d		V _{DS} = 30 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
		V _{GS} = 10 V, I _D = 10 A	0.008				
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 9 A		0.011		Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 10 A		50		S	
Dynamic ^b	1						
Input Capacitance	C _{iss}			800		pF	
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		165			
Reverse Transfer Capacitance	C _{rss}			73			
T. 10 . 0		V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A		15	23	nC	
Total Gate Charge				6.8	10.2		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 10 \text{ A}$		2.5			
Gate-Drain Charge	Q_{gd}			2.3		1	
Gate Resistance	R_g	f = 1 MHz	0.36	1.8	3.6	Ω	
Turn-On Delay Time	t _{d(on)}			16	23		
Rise Time	t _r	V_{DD} = 15 V, R_L = 1.4 Ω		12	16	1	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 9 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		16	22	1	
Fall Time	t _f			10	18	1	
Turn-On Delay Time	t _{d(on)}			8	16	ns	
Rise Time	t _r	V_{DD} = 15 V, R_L = 1.4 Ω		10	20		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 9 \text{ A}, \ V_{GEN} = 10 \text{ V}, \ R_g = 1 \ \Omega$		16	22		
Fall Time	t _f			8	15	1	
Drain-Source Body Diode Characterist	ics			1	'		
Continuous Source-Drain Diode Current	IS	T _C = 25 °C			10		
Pulse Diode Forward Current ^a	I _{SM}				50	_ A	
Body Diode Voltage	V_{SD}	I _S = 9 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			15	30	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 9 A, dl/dt = 100 A/μs, T _J = 25 °C		6	12	nC	
Reverse Recovery Fall Time	t _a			8			
Reverse Recovery Rise Time	t _b		7			ns	

Notes:

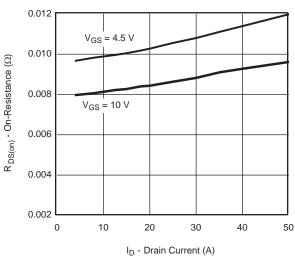
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

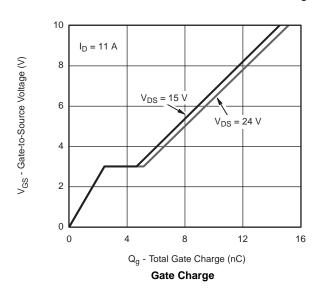




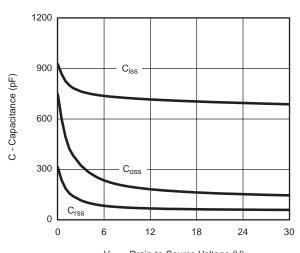
Output Characteristics



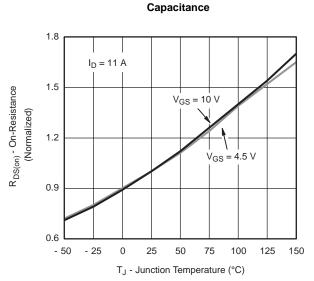
On-Resistance vs. Drain Current and Gate Voltage



V_{GS} - Gate-to-Source Voltage (V) **Transfer Characteristics**

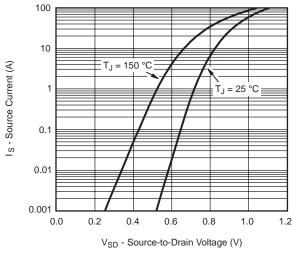


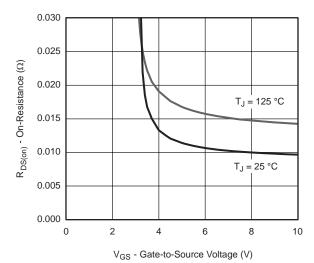
V_{DS} - Drain-to-Source Voltage (V)



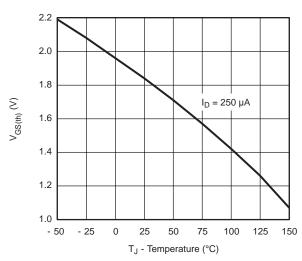
On-Resistance vs. Junction Temperature



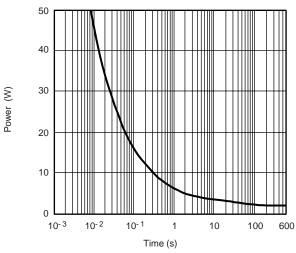




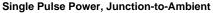
Source-Drain Diode Forward Voltage

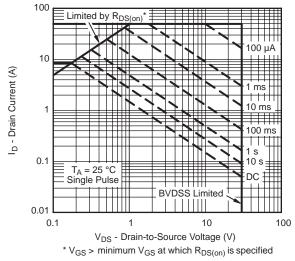


On-Resistance vs. Gate-to-Source Voltage



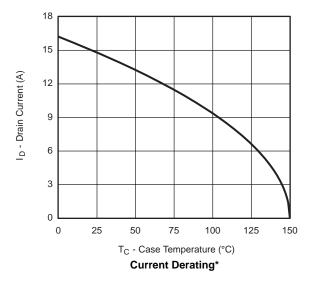
Threshold Voltage

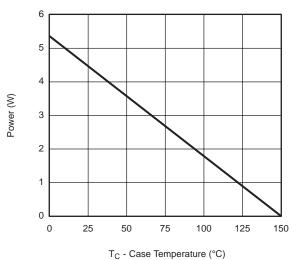


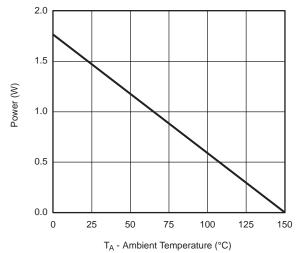


Safe Operating Area, Junction-to-Ambient









Power Derating, Junction-to-Foot

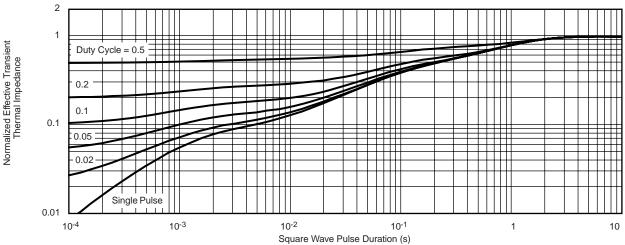
Power Derating, Junction-to-Ambient

^{*} The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





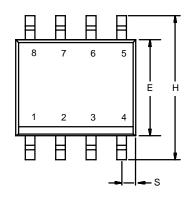
Normalized Thermal Transient Impedance, Junction-to-Ambient

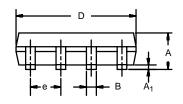


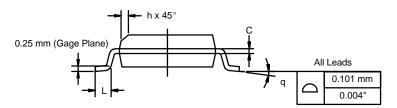
Normalized Thermal Transient Impedance, Junction-to-Foot



SOIC (NARROW): 8-LEAD







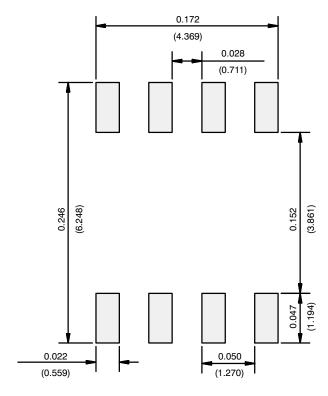
	MILLIM	IETERS	INC	HES	
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
FCN: C-06527-Rev I 11-Sen-06					

ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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